

SEMICONDUCTOR
TECHNICAL DATA

KTC4372

TRIPLE DIFFUSED NPN TRANSISTOR

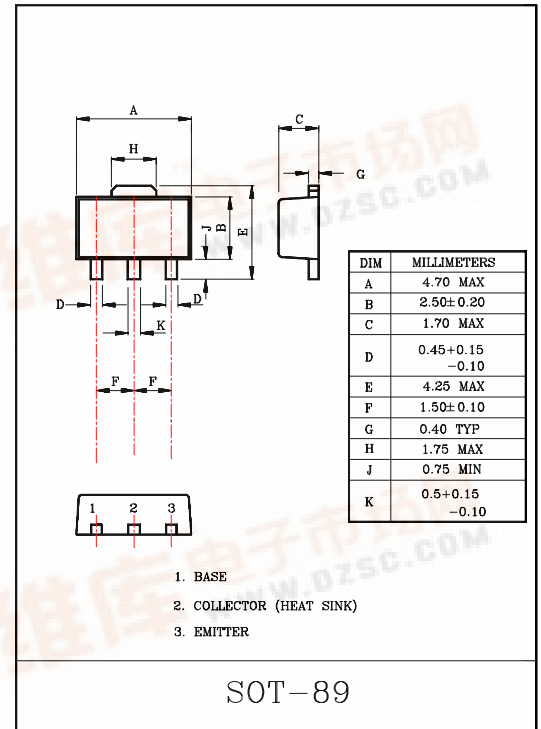
HIGH VOLTAGE SWITCHING APPLICATION.

FEATURES

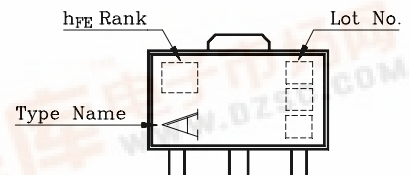
- High Voltage : $V_{CEO}=150V$.
- High Transition Frequency : $f_T=120MHz$.
- 1W (Mounted on Ceramic Substrate).
- Small Flat Package.
- Complementary to KTA1660.

MAXIMUM RATINGS ($T_a=25^\circ C$)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	V_{CBO}	200	V
Collector-Emitter Voltage	V_{CEO}	150	V
Emitter-Base Voltage	V_{EBO}	5	V
Collector Current	I_C	50	mA
Base Current	I_B	10	mA
Collector Power Dissipation	P_C	500	mW
	P_{C^*}	1	W
Junction Temperature	T_j	150	$^\circ C$
Storage Temperature Range	T_{stg}	-55 ~ 150	$^\circ C$

 P_{C^*} KTC4372 mounted on ceramic substrate (250mm²x0.8t)

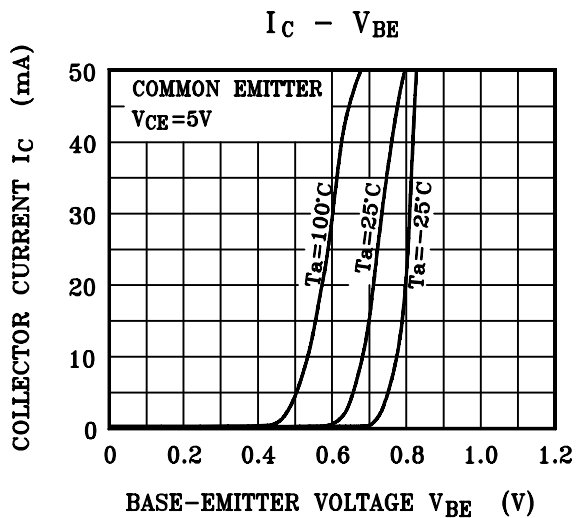
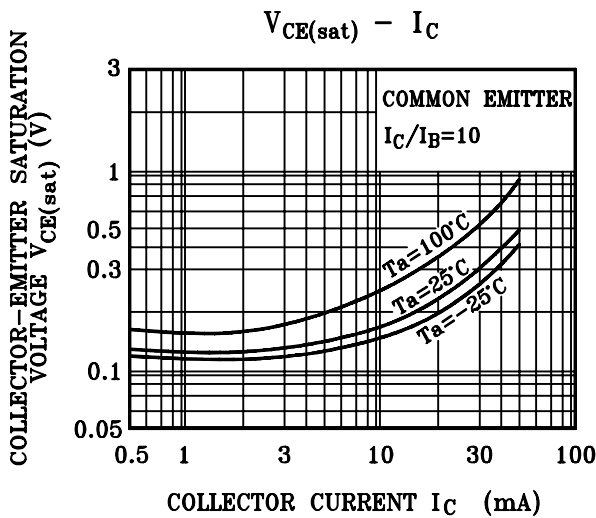
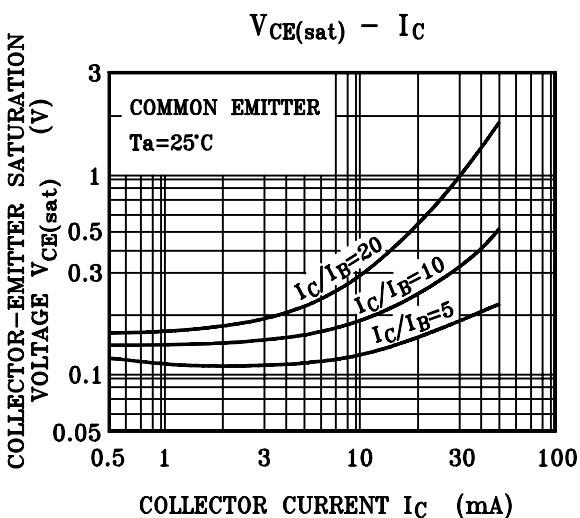
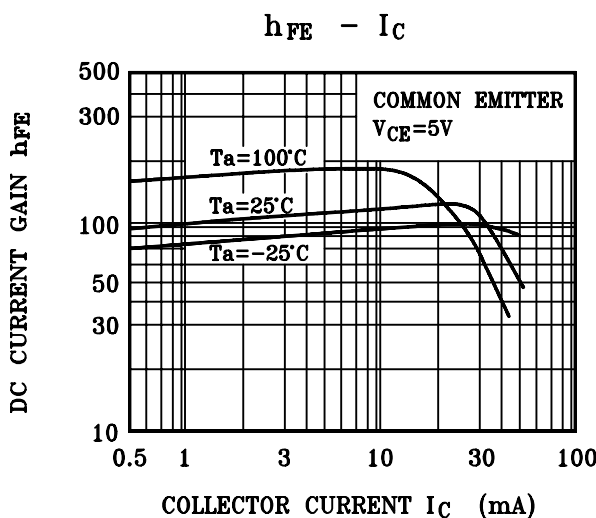
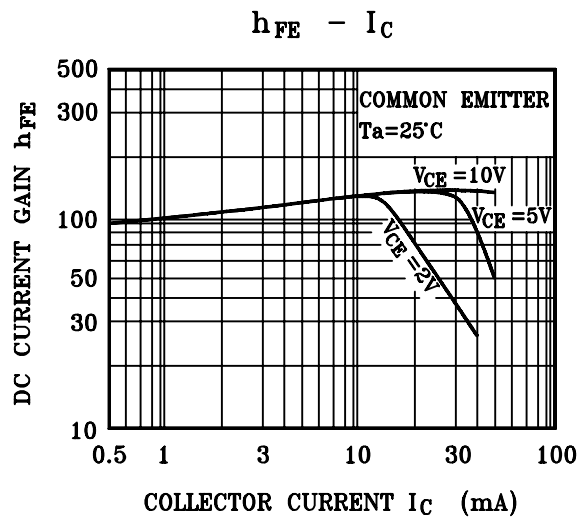
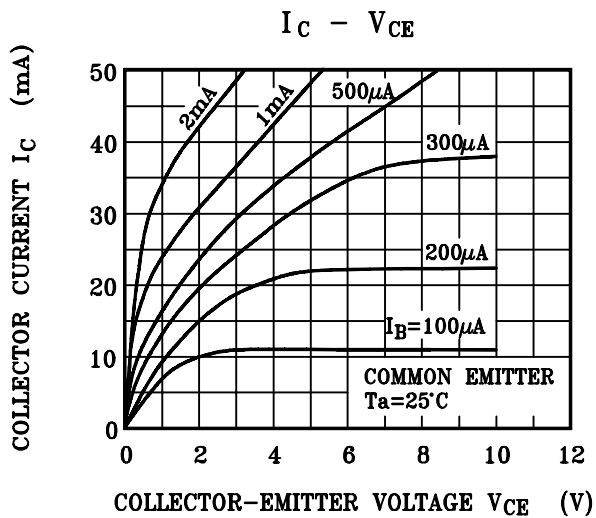
Marking

ELECTRICAL CHARACTERISTICS ($T_a=25^\circ C$)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current	I_{CBO}	$V_{CB}=200V, I_E=0$	-	-	0.1	μA
Emitter Cut-off Current	I_{EBO}	$V_{EB}=5V, I_C=0$	-	-	0.1	μA
DC Current Gain	$h_{FE}(\text{Note})$	$V_{CE}=5V, I_C=10mA$	70	-	240	
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C=10mA, I_B=1mA$	-	-	0.5	V
Base-Emitter Voltage	V_{BE}	$V_{CE}=5V, I_C=30mA$	-	-	1.0	V
Transition Frequency	f_T	$V_{CE}=30V, I_C=10mA$	-	120	-	MHz
Collector Output Capacitance	C_{ob}	$V_{CB}=10V, I_E=0, f=1MHz$	-	3.5	5.0	pF

Note : h_{FE} Classification O:70~140, Y:120~240

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